

10 GHz, Integer-N/Fractional-N PLL Synthesizer

FEATURES

- ▶ 1 GHz to 10 GHz bandwidth
- ▶ Ultra-low noise phase locked loop (PLL)
- ► Integer-N = -235 dBc/Hz, fractional-N = -231 dBc/Hz
- High maximum phase frequency detector (PFD) frequency
 - Integer-N = 250 MHz, fractional-N = 125 MHz
- 25-bit fixed/49-bit variable fractional modulus mode
- ▶ Single-ended reference input
- ▶ 3.3 V power supply, 3.3 V charge pump
- Integrated 1.8 V logic capability
- Phase resync
- Programmable charge pump currents: 16× range
- Digital lock detect (DLD)
- 3-wire serial interface with register readback option
- Hardware and software power-down mode
- ▶ Operating range: -40°C to +105°C

APPLICATIONS

- Test equipment and instrumentation
- Wireless infrastructure
- Microwave point-to-point and multipoint radios
- Very small aperture terminal (VSAT) radios
- Aerospace and defense

FUNCTIONAL BLOCK DIAGRAM

GENERAL DESCRIPTION

The ADF41510 is an ultra-low noise frequency synthesizer that can be used to implement local oscillators (LOs) as high as 10 GHz in the upconversion and downconversion sections of wireless receivers and transmitters.

The ADF41510 is designed on a high-performance silicon germanium (SiGe), bipolar complementary metal-oxide semiconductor (BiCMOS) process, achieving a normalized phase noise floor of -235 dBc/Hz. The PFD operates up to 250 MHz (integer-N mode)/125 MHz (fractional-N mode) for improved phase noise and spur performance. The variable modulus, Σ - Δ modulator, allows extremely fine resolution when using a 49-bit divide value. The ADF41510 can be used as an integer-N PLL, or it can be used as a fractional-N PLL with either a fixed modulus for subhertz frequency resolution or variable modulus for subhertz exact frequency resolution.

A complete PLL is implemented when the synthesizer is used with an external loop filter and voltage-controlled oscillator (VCO). The 10 GHz bandwidth eliminates the need for a frequency doubler or divider stage, simplifying system architecture and reducing cost. The ADF41510 is packaged in a compact, 24-lead, 4 mm × 4 mm LFCSP.

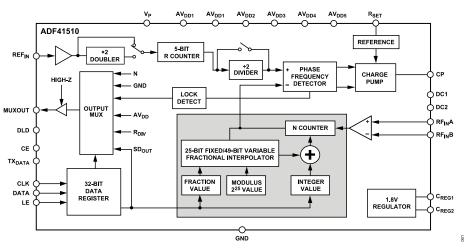


Figure 1. Functional Block Diagram

Rev. 0

DOCUMENT FEEDBACK

Information furnished by Analog Devices is believed to be accurate and reliable "as is". However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.

TABLE OF CONTENTS

Features	1
Applications	1
General Description	1
Functional Block Diagram	1
Specifications	3
Timing Characteristics	4
Absolute Maximum Ratings	6
Thermal Resistance	6
ESD Caution	6
Pin Configuration and Function Description	7
Typical Performance Characteristics	8
Theory of Operation	
Reference Input	
RF Input Stage	
N Divider and R Counter	
R Counter	11
PFD and Charge Pump	
MUXOUT	11
Lock Detector	11
Readback	12
Input Shift Registers	
Program Modes	12
Register Maps	
Register 0 (R0) Map	
Register 1 (R1) Map	15

REVISION HISTORY

2/2024—Revision 0: Initial Version

Register 2 (R2) Map	16
Register 3 (R3) Map	
Register 4 (R4) Map	
Register 5 (R5) Map	
Register 6 (R6) Map	
Register 7 (R7) Map	
Register 8 (R8) Map	
Register 9 (R9) Map	
Register 10 (R10) Map	
Register 11 (R11) Map	
Register 12 (R12) Map	
Register 13 (R13) Map	
Applications information	
Initialization Sequence	27
RF Synthesizer: A Worked Example of 25-	
Bit Fixed Modulus Mode	27
RF Synthesizer: A Worked Example of	
Variable Modulus Mode	27
Modulus	27
Reference Doubler and Reference Divider	27
Spur Mechanisms	27
Phase Resync	28
Outline Dimensions	29
Ordering Guide	29
Evaluation Boards	29

SPECIFICATIONS

 $AV_{DDx} = AV_{DD1} = AV_{DD2} = AV_{DD3} = AV_{DD4} = AV_{DD5} = V_P = 3.3 V \pm 5\%$, GND = 0 V, $R_{SET} = 1.8 k\Omega$, dBm referred to 50 Ω , $T_A = T_{MIN}$ (-40°C) to T_{MAX} (+105°C), unless otherwise noted.

Table 1. Specifications

Parameter	Min	Тур	Max	Unit	Test Conditions/Comments
RADIO FREQUENCY (RF) CHARACTERISTICS					
RF Input Sensitivity		-11		dBm	See Figure 9 and Figure 10 for more information
f _{RFIN} Range	1		10	GHz	For lower frequencies, ensure slew rate > 320 V/us
RF Input Sensitivity Range	-7		+5	dBm	Measured single-ended to RF _{IN} A through a 1 pF series
	-/		+0	ubiii	capacitor, 1 pF capacitor to GND on RF _{IN} B
INPUT REFERENCE FREQUENCY (REF _{IN}) CHARACTERISTICS					
REF _{IN} Input					
Frequency	10		800	MHz	
Voltage Range	0		1.8	V	
Sensitivity Range	-10		+8	dBm	Biased at 1 V (AC coupling ensures 1 V bias), use square wave at low power and/or frequency to ensure slew rate is > 320 V/µs; for best in-band phase noise performance, ensure slew rate > 500 V/µs
Capacitance			10	pF	
Current			±150	μA	
Doubler Input Frequency			225	MHz	Maximum reference frequency when the doubler is enabled
MAXIMUM PFD FREQUENCY					
Integer-N Mode			250	MHz	
Fractional-N Mode			125	MHz	
N DIVIDER RANGE					
16-Bit N Divider Range					
Integer-N Mode	20		511		
Fractional-N Mode	23		511		
CHARGE PUMP (CP)					
CP Current (I _{CP}) Sink and Source					Programmable
High Value		7.2		mA	With $R_{SET} = 1.8 \text{ k}\Omega$
Low Value		0.45		mA	THAT SET TO KE
Absolute Accuracy		5		%	With $R_{SET} = 1.8 \text{ k}\Omega$
R _{SET} Range	1.8	2.7	10	kΩ	5% accuracy
I _{CP} Three-State Leakage	1.0	2	10	nA	$V_{CP} = 0.9 \text{ V}, T_A = 25^{\circ}\text{C}$
Sink and Source Current Matching		5		%	$0.7 \text{ V} \le \text{CP}$ voltage (V _{CP}) $\le \text{V}_{\text{P}} - 0.7 \text{ V}$
I _{CP} vs. V _{CP}		5		%	$0.7 V \le V_{CP} \le V_P - 0.7 V$
I _{CP} vs. Temperature		5		%	$V_{CP} = V_{P}/2$
		•		70	
Input Voltage					
High (V _{IH})	1.4			V	The serial port interface (SPI) block can accept both 1.8 V or
	1.4				3.3 V logic inputs
Low (V _{IL})			0.6	V	
Input Current (I _{INH} , I _{INL})			±1	μA _	
Input Capacitance (C _{IN})			10	pF	
LOGIC OUTPUTS					
Output Voltage					
High (V _{OH})	1.4			V	MUXOUT voltage = 1.8 V, DLD voltage = 1.8 V
	2.6			V	MUXOUT voltage = 3.3 V, DLD voltage = 3.3 V
Low (V _{OL})			0.4	V	

SPECIFICATIONS

Table 1. Specifications (Continued)

Parameter	Min	Тур	Max	Unit	Test Conditions/Comments
Output High Current, Output Low Current (I_{OH}, I_{OL})			500	μA	
POWER SUPPLIES					
AV_{DD1} , AV_{DD2} , AV_{DD3} , AV_{DD4} , AV_{DD5} , V_P	3.135	3.3	3.465	V	
I _{DD1} ¹		2	3.2	mA	Current drawn by AV _{DD1}
I _{DD2} ¹		63.5	88	mA	Current drawn by AV _{DD2}
I _{DD3} ¹		2.1	3.6	mA	Current drawn by AV _{DD3}
I _{DD4} ¹		1.45	2	mA	Current drawn by AV _{DD4}
I _{DD5} ¹		20	25	mA	Current drawn by AV _{DD5}
I _P		6	7	mA	Current drawn by V _P
I _{TOTAL}		95.1	128.8	mA	Total current drawn by AV_{DDx} and V_P
Power-Down Mode			100	μA	$T_A = 25^{\circ}C$, CE is low, total of all rails
NOISE CHARACTERISTICS					
Normalized Phase Noise Floor (PN _{SYNTH})					
In Integer-N Mode ²		-235		dBc/Hz	PLL loop bandwidth (BW) = 1 MHz (Integer-N mode)
In Fractional-N Mode ³		-231		dBc/Hz	PLL loop BW = 1 MHz (Fractional-N mode)
Normalized 1/f Noise $(PN_{1_f})^3$		-128		dBc/Hz	10 kHz offset, normalized to 1 GHz
SPURIOUS SIGNALS					
Reference Spurious		-90		dBc	At reference = 100 MHz, PLL loop BW = 40 kHz
PFD Spurious		-87		dBc	At PFD = 50 MHz, PLL loop BW = 40 kHz
In-Band Integer Boundary Spurious		-45		dBc	10 kHz offset, PLL loop BW = 250 kHz

¹ $T_A = 25^{\circ}C$, $AV_{DDx} = 3.3 V$ (where x = 1, 2, 3, or 4), $f_{RFIN} = 10 \text{ GHz}$, $REF_{IN} = 100 \text{ MHz}$, PFD frequency input (f_{PFD}) = 100 MHz.

² The synthesizer phase noise floor is estimated by measuring the in-band phase noise at the output of the VCO and subtracting 20 log N (where N is the N divider value) and 10 log f_{PFD}. PN_{SYNTH} is the total phase noise measured at the VCO output (PN_{TOT}) – 10 log f_{PFD} – 20 log N.

³ The PLL phase noise is composed of 1/f (flicker) noise plus the normalized PLL noise floor. The formula for calculating the 1/f noise contribution at an RF output frequency, f_{RF}, and at a frequency offset, f, is given by phase noise (PN) = P_{1_f} + 10 log(10 kHz/f) + 20 log(f_{RF}/1 GHz). Both the normalized phase noise floor and flicker noise are modeled in ADIsimPLL.

TIMING CHARACTERISTICS

 $AV_{DDx} = AV_{DD1} = AV_{DD2} = AV_{DD3} = AV_{DD4} = AV_{DD5} = V_P = 3.3 V \pm 5\%$, GND = 0 V, $R_{SET} = 1.8 k\Omega$, dBm referred to 50 Ω , $T_A = T_{MIN}$ (-40°C) to T_{MAX} (+105°C), unless otherwise noted.

Parameter	Limit at T _{MIN} to T _{MAX}	Unit	Test Conditions/Comments
t ₁	10	ns min	LE setup time
t ₂	5	ns min	DATA to CLK setup time
t ₃	5	ns min	DATA to CLK hold time
t ₄	12.5	ns min	CLK high duration
t ₅	12.5	ns min	CLK low duration
t ₆	5	ns min	CLK to LE setup time
t ₇	10	ns min	LE pulse width
t ₈	20	ns max	LE setup time to MUXOUT when MUXOUT is configured as SPI output
t ₉	20	ns max	CLK setup time to MUXOUT when MUXOUT is configured as SPI output

Table 2. Read and Write Timing

SPECIFICATIONS

Timing Diagram

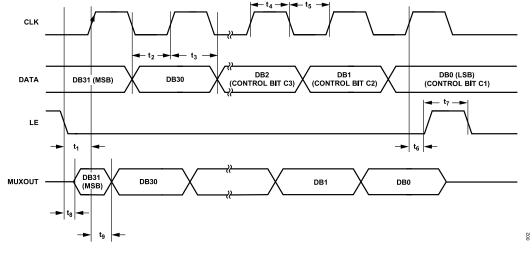


Figure 2. Read and Write Timing

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}C$, unless otherwise noted.

Table 3. Absolute Maximum Ratings

Parameter	Rating
AV _{DDx} to GND ¹	-0.3 V to +3.6 V
V _P to GND	-0.3 V to +3.6 V
V _P to AV _{DDx}	-0.3 V to +0.3 V
Digital Input/Output Voltage to GND	-0.3 V to AV _{DDx} + 0.3 V
Analog Input/Output Voltage to GND	-0.3 V to V _P + 0.3 V
RF _{IN} A, RF _{IN} B to GND	-0.3 V to +3.6 V
RF _{IN} A to RF _{IN} B ¹	±1.4 V
REF _{IN} to GND	-0.3 V to +2.1 V
Operating Temperature Range	
Industrial	-40°C to +105°C
Storage Temperature Range	-65°C to +125°C
Maximum Junction Temperature	
Operational	125°C
Reflow Soldering	
Peak Temperature	260°C
Time at Peak Temperature	40 sec
Electrostatic Discharge (ESD)	
Charged Device Model	1250 V
Human Body Model	1500 V
Transistor Count	
CMOS	215,726
Bipolar	1625

THERMAL RESISTANCE

Thermal performance is directly linked to printed circuit board (PCB) design and operating environment. Careful attention to PCB thermal design is required.

 θ_{JA} is the natural convection junction to ambient thermal resistance measured in a one cubic foot sealed enclosure. θ_{JC} is the junction to case thermal resistance.

Table 4. Thermal Resistance

Package Type	θ _{JA}	θ _{JC}	Unit
CP-24-8 ¹	48	38	°C/W

¹ The thermal resistance values are defined per the JESD51 standard.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

¹ Approximately 13 dBm into a 50 Ω input.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

This device is a high performance RF integrated circuit with an ESD rating of <2 kV, and the device is ESD sensitive. Take proper precautions for handling and assembly.

PIN CONFIGURATION AND FUNCTION DESCRIPTION

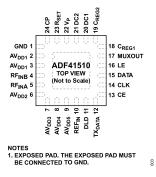


Figure 3. Pin Configuration

Table 5. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	GND	Ground Pin.
2, 3	AV _{DD1}	PFD and Up and Down Digital Driver Power Supply. Pin 2 and Pin 3 can be tied together. With Pin 2 and Pin 3 tied together, place three parallel capacitors as close as possible to the AV _{DD1} pins: 10 μF, 100 nF, and 100 pF.
4	RF _{IN} B	Complementary Input to the RF Prescaler. In single-ended mode, decouple this pin to the ground plane with a small bypass capacitor, typically 100 pF.
5	RF _{IN} A	Input to the RF Prescaler. AC-couple this signal to the external VCO.
6	AV _{DD2}	RF Buffer and Prescaler Power Supply. Place three parallel capacitors as close as possible to the AV _{DD2} pin: 10 µF, 100 nF, and 100 pF.
7	AV _{DD3}	N Divider Power Supply. Place three parallel capacitors as close as possible to the AV _{DD3} pin: 10 µF, 100 nF, and 100 pF.
8	AV _{DD4}	R Divider and Lock Detector Power Supply. Place three parallel capacitors as close as possible to the AV _{DD4} pin: 10 µF, 1 µF, and 100 nF. Pin 8 powers the internal low dropout (LDO) regulator for the reference divider.
9	AV _{DD5}	Σ -Δ Modulator and SPI Power Supply. Place three parallel capacitors as close as possible to the AV _{DD5} pin: 10 µF, 1 µF, and 100 nF. This pin powers the internal LDO regulator for the Σ -Δ modulator.
10	REF _{IN}	Reference Input. The reference can accept either a single-ended CMOS (DC-coupled) or single-ended sine wave (AC-coupled). The single-ended input has a nominal threshold of 1 V and a DC equivalent input resistance of 20 k Ω .
11	DLD	Digital Lock Detect Pin. A logic high on this pin indicates PLL lock.
12	TX _{DATA}	Transmit Data Pin. Pin 12 is not used. Connect Pin 12 to GND.
13	CE	Chip Enable. A logic low on this pin powers down the device and puts the charge pump output into three-state mode. Registers do not hold their values when CE is low. This pin only supports 3.3 V logic inputs.
14	CLK	Serial Clock Input. CLK clocks in the serial data to the registers. The data is latched into the 32-bit shift register on the CLK rising edge. This input is a high-impedance CMOS input.
15	DATA	Serial Data Input. The serial data is loaded most significant bit (MSB) first with the two least significant bits (LSBs) as the control bits. This input is a high-impedance CMOS input.
16	LE	Load Enable, CMOS Input. When LE goes high, the data stored in the shift registers is loaded into one of the four latches. Select the latch using the control bits.
17	MUXOUT	Multiplexer Output. This multiplexer output allows the lock detect, the scaled RF, the scaled reference frequency, logic high, logic low, or register readback data to be accessed externally.
18	C _{REG1}	Internal 1.8 V Regulator Output Pin. Place three parallel capacitors as close to the C _{REG1} pin as possible: 4.7 µF, 100 nF, and 1 nF.
19	C _{REG2}	Internal 1.8 V Regulator Output Pin. Place three parallel capacitors as close to the CREG2 pin as possible: 4.7 µF, 100 nF, and 1 nF.
20	DC1	DC Bias Pin 1. Place a 1 µF capacitor in parallel with a 1 nF capacitor to ground, as close as possible to the DC1 pin.
21	DC2	DC Bias Pin 2. Place a 1 µF capacitor in parallel with a 1 nF capacitor to ground, as close as possible to the DC2 pin.
22	VP	Charge Pump Power Supply.
23	R _{SET}	Maximum Charge Pump Current Setting Resistor. Connecting a resistor between the R_{SET} pin and GND sets the maximum charge pump output current. The nominal voltage potential at the R_{SET} pin is 0.66 V. The relationship between I_{CP} and R_{SET} is I_{CP_MAX} = 12.96/ R_{SET} . For example, with R_{SET} = 2.7 k Ω , I_{CP_MAX} = 4.8 mA. The relationship between bleed current (I_{BLEED}) and R_{SET} is I_{BLEED_MIN} = 0.0103/ R_{SET} . For example, with R_{SET} = 2.7 k Ω , I_{BLEED_MIN} = 3.81 μ A.
24	CP	Charge Pump Output. When enabled, this pin provides ±I _{CP} to the external loop filter, which in turn drives the external VCO.
	EPAD	Exposed Pad. The exposed pad must be connected to GND.

TYPICAL PERFORMANCE CHARACTERISTICS

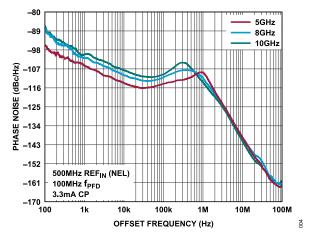


Figure 4. Phase Noise vs. Offset Frequency Using HMC587 VCO, Integer-N Mode

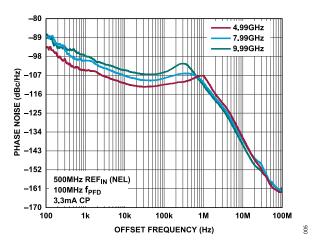


Figure 5. Phase Noise vs. Offset Frequency Using HMC587 VCO, Fractional-N Mode

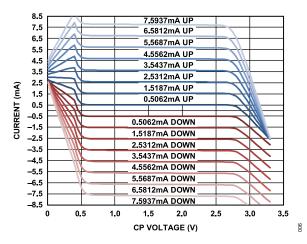


Figure 6. Current vs. CP Voltage, Charge Pump Compliance, R_{SET} = 1.8 kΩ

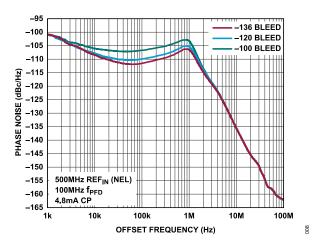


Figure 7. 7.99 GHz Phase Noise vs. Offset Frequency across Current Bleed, Fractional-N Mode

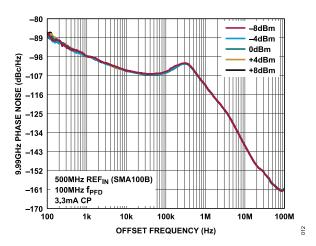


Figure 8. Phase Noise vs. Offset Frequency across REF_{IN} Powers, Fractional-N Mode

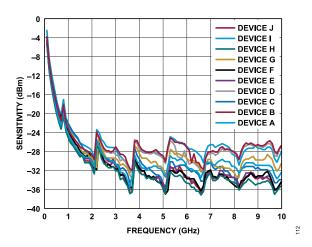


Figure 9. Sensitivity vs. Frequency across Soldered Devices

TYPICAL PERFORMANCE CHARACTERISTICS

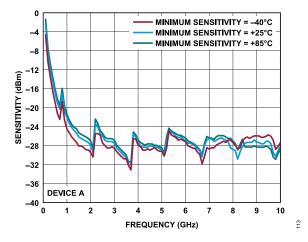


Figure 10. Sensitivity vs. Frequency across Temperatures

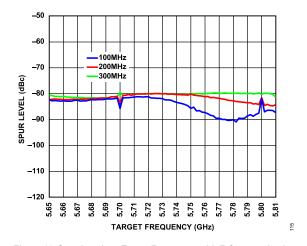


Figure 11. Spur Level vs. Target Frequency with Z-Communications V940ME03 VCO, REF_{IN} = 100 MHz, PFD = 100 MHz, PLL Loop BW = 80 kHz

THEORY OF OPERATION

REFERENCE INPUT

The reference input stage is shown in Figure 12. The reference input accepts an AC-coupled, single-ended signal. During powerdown, this circuit remains active and draws the same current from AV_{DD4} as during normal operation. With no reference connected, AV_{DD4} drops to approximately 600 μ A.

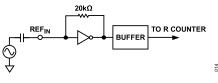
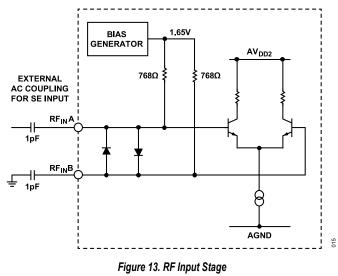


Figure 12. Reference Input Stage

RF INPUT STAGE

The RF input stage is shown in Figure 13. A two-stage limiting amplifier follows the RF input stage to generate the current mode logic (CML) clock levels needed for the prescaler. The RF_{IN}A and RF_{IN}B inputs require DC blocking capacitors to isolate the 1.65 V bias level from the input signal.



N DIVIDER AND R COUNTER

The N divider is used to divide the RF input signal down to the PFD frequency ($f_{\text{PFD}}).$

$$f_{PFD} = REF_{IN} \times ((1 + D)/(R \times (1 + T)))$$
(1)

where:

*REF*_{*IN*} is the reference input frequency.

D is the REF_{IN} doubler bit value (0 or 1).

R is the preset divide ratio of the binary 5-bit programmable reference counter (1 to 32).

T is the REF_{IN} divide by 2-bit value (0 or 1).

The N divider value is generated by a Σ - Δ modulator. The ADF41510 contains two selectable Σ - Δ modulators. One modulator has a 25-bit fixed modulus (see Figure 14) and one has a variable

analog.com

modulus up to 49 bits (see Figure 15). Register 0, Bit 28 selects the modulator.

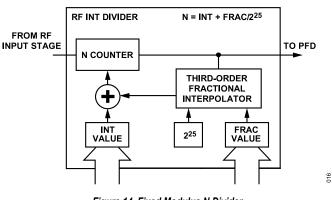


Figure 14. Fixed Modulus N Divider

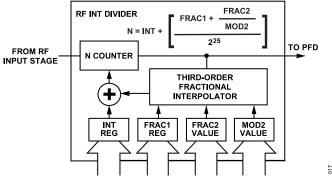


Figure 15. Variable Modulus N Divider

25-Bit Fixed Modulus (Register 0, Bit 28 = 0)

For the 25-bit fixed modulus, the RF VCO frequency $(\mathrm{RF}_{\mathrm{OUT}})$ equation is

$$RF_{OUT} = f_{PFD} \times (INT + (FRAC/2^{25}))$$
⁽²⁾

where:

RFOUT is the RF VCO frequency.

INT is a 16-bit value set by Bits[19:4] in Register 0. In Integer-N mode, *INT* is 20 to 511, and in Fractional-N mode, *INT* is 23 to 511. *FRAC* is a 25-bit value set by Bits[28:4], FRAC1, in Register 1.

The minimum RF output resolution is set by $f_{PFD}/2^{25}$. For example, if f_{PFD} = 100 MHz, the minimum resolution is 2.98 Hz.

By default, due to the architecture of the Σ - Δ modulator, there is a fixed (f_{PFD}/2²⁶) offset added or subtracted from the programmed output frequency. To remove this offset, set LSB_PI (Register 5, Bit 24).

Variable Modulus (R0, DB28 = 1)

For the variable modulus, the RF VCO frequency $(\mathrm{RF}_{\mathrm{OUT}})$ equation is

$$RF_{OUT} = f_{PFD} \times (INT + (FRAC1 + (FRAC2/MOD2))/2^{25})$$
(3)

THEORY OF OPERATION

where:

 RF_{OUT} is the output frequency of external VCO. INT is a 16-bit value set by Bits[19:4] in Register 0. In Integer-N mode, INT is 20 to 511, and in Fractional-N mode, INT is 23 to 511. FRAC1 is a 25-bit value set by Bits[28:4] in Register 1. FRAC2 is a 24-bit value set by Bits[27:4] in Register 3. MOD2 is a 24-bit value set by Bits[27:4] in Register 4.

The minimum RF output resolution is set by $f_{PFD}/2^{49}$. Therefore, for f_{PFD} = 100 MHz, the minimum resolution is 0.1776 µHz. To achieve this resolution, MOD2 must be set to its maximum of (2^{24} – 1), which is 16,777,215.

Integer-N Mode

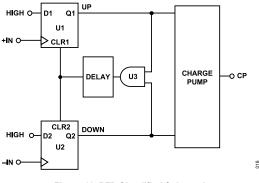
When FRAC1 and FRAC2 are both equal to 0, the ADF41510 can operate in purely Integer-N mode, which improves the phase noise performance of the PLL and sets the frequency resolution to f_{PFD} . This feature is not automatic and must be manually set for Integer-N channels. Bleed must also be disabled when using the ADF41510 in Integer-N operation. See the Register 6 (R6) Map section for more information on programming the ADF41510 for Integer-N operation.

R COUNTER

The 5-bit R counter allows REF_{IN} to be divided down to produce the reference clock to the PFD. Division ratios from 1 to 32 are allowed.

PFD AND CHARGE PUMP

The PFD takes inputs from the R counter and N counter and produces an output proportional to the phase and frequency difference between these inputs. Figure 16 shows a PFD simplified schematic. The PFD includes a fixed delay element that sets the width of the anti-backlash pulse, which is typically 1 ns. This pulse ensures that there is no dead zone in the PFD transfer function and produces a consistent reference spur level.





MUXOUT

The output multiplexer on the ADF41510 allows the user to access various internal nodes on the chip. The M4, M3, M2, and M1 bits in Register 12 (see the Register 12 (R12) Map section) controls

the state of MUXOUT. Figure 17 shows the MUXOUT section in block diagram form. Many of these access points are useful for debugging. For example, select the N-divider output to check if the N divider is functioning correctly. Most of the access points are self explanatory. Set the CLK₁ divider output signal to access the internal CLK₁ divider signal used for phase resync. During power-down (CE = logic low), MUXOUT is set to GND.

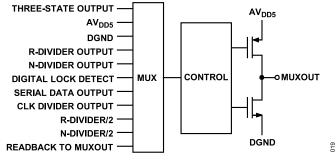


Figure 17. MUXOUT Schematic

LOCK DETECTOR

The lock detector compares the PFD output pulse width against a lock detector window. Measurements are performed every PFD comparison cycle when LD_CLK_SEL = 1 or every 32nd cycle when LD_CLK_SEL = 0. If the pulse width falls within the lock window, a counter is incremented. If the counter reaches the count set by LD_COUNT without an up or down pulse width exceeding the lock detect window and without a cycle slip occurring, lock is then declared by the lock detector.

When the lock detector has declared lock, the main mechanism to declare a loss of lock is for a cycle slip to occur. This cycle slip is usually caused by a frequency error at the phase detector input, causing the phase error to grow until the error exceeds 360° . The phase error then wraps around to 0° . This phase wraparound is a cycle slip.

A high level on MUXOUT indicates that the PLL is in lock.

The lock detector window size, LD_COUNT, and LD_CLK_SEL all affect the sensitivity of the lock detector. Larger windows, smaller LD_COUNT values, and LD_CLK_SEL = 0 shorten the overall lock detect time and increase sensitivity. Smaller windows, larger LD_COUNT values, and LD_CLK_SEL = 1 increase the overall lock detect time and reduce sensitivity. Excessive lock detector sensitivity can cause multiple transitions between a locked state and out-of-lock state during frequency changes. Insufficient lock detector sensitivity can cause the detector to indicate an out-of-lock state when, in fact, the PLL is locked.

The window size can be adjusted between 0.9 ns and 11.5 ns with LDP, Bits[9:8] in Register 6 and LD bias, Bits[31:30] in Register 9. The ideal window size is halfway between the maximum window, set by the phase comparison period, t_{PFD} (10 ns for 100 MHz reference and R = 1), and the minimum is set by

THEORY OF OPERATION

$(I_{BLEED}/I_{CP}) \times t_{PFD}$

LD_COUNT can range from 2 counts to 8192 counts. The fastest lock indication requires two measurement cycles (20 ns with 100 MHz reference, R = 1, and LD_CLK_SEL = 1). In practice, the lock indication takes much longer because of the loop filter on the phase comparator. When LD_CLK_SEL = 0, a minimum 64 measurements are required (640 ns).

READBACK

Register data can be read by setting MUXOUT to serial data output. In this mode, the MUXOUT line concurrently transfers 32 bits of the previous written register value while clocking in 32 bits of write data.

To read back a specific register, chip revision code, or bit pattern, write 1000b to Bits[31:28], Register 12. Bits[19:14] in Register 12 set the data that is output from the MUXOUT pin when in readback mode.

To prevent spurious writes, the DATA pin must be held at logic low while a readback is taking place.

INPUT SHIFT REGISTERS

The ADF41510 contains a programmable digital block. Data is clocked into the 32-bit shift register on each rising edge of CLK. The data is clocked in MSB first. Data is transferred from the shift register to the chosen register on the rising edge of LE. The destination latch is determined by the state of the four control bits (C4, C3, C2, and C1) in the shift register. The following are the four LSBs: DB3, DB2, DB1, and DB0. The truth table for these bits is shown in Table 6. Figure 18 through Figure 20 show a summary of how the registers are programmed.

PROGRAM MODES

Table 6 and Figure 21 through Figure 34 show how to set up the program modes in the ADF41510.

Several settings in the ADF41510 are double buffered. These settings include MOD2, FRAC1, FRAC2, R counter value, reference doubler, CP current setting, RDIV2, phase word, prescaler, and CLK_1 divider. Two events must occur before the device uses a new value for any of the double buffered settings. First, the new value is latched into the device by writing to the appropriate register. Second, a new write must be performed on Register 0. For example, updating the FRAC1 value requires a write to Register 1 and a write to Register 0. Write to Register 1 first, followed by the write to Register 0. The frequency change begins after the write to Register 0. Double buffering ensures that the bits written to Register 1 do not take effect until after the write to Register 0.

(4)

Table 6. C4, C3, C2, and C1 Truth Table

	Co	ontrol Bits			
C4	C3	C2	C1	Register	
0	0	0	0	R0	
0	0	0	1	R1	
0	0	1	0	R2	
0	0	1	1	R3	
0	1	0	0	R4	
0	1	0	1	R5	
0	1	1	0	R6	
0	1	1	1	R7	
1	0	0	0	R8	
1	0	0	1	R9	
1	0	1	0	R10	
1	0	1	1	R11	
1	1	0	0	R12	
1	1	0	1	R13	

Data Sheet

INT REGISTER (R0)

F	RESER	VED	VARIABLE MODULUS				RESE	RVED				16-BIT INTEGER VALUE (INT)													ITROL ITS						
DB3	1 DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB 14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
0	0	0	V1	0	0	0	0	0	0	0	0	N16	N15	N14	N13	N12	N11	N10	N9	N8	N7	N6	N5	N4	N3	N2	N1	C4(0)	C3(0)	C2(0)	C1(0)

	FRAC1 REGISTER (R1)																														
DITHER2		DBB 25-BIT FRAC1 VALUE (FRAC1)															DBB		CON BI	TROL TS											
DB3	1 DB30	DB29	DB28	DB 27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB 14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
D1	0	0	F25	F24	F23	F22	F21	F20	F19	F18	F17	F16	F15	F14	F13	F12	F11	F10	F9	F8	F7	F6	F5	F4	F3	F2	F1	C4(0)	C3(0)	C2(0)	C1(1)

	PHASE REGISTER (R2)																														
PHASE ADJUST		RESERVED																	12-	BIT PH	IASE V	/ALUE	(PHA:	SE)		[DBB		CON BI		
DB31	DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB 16	DB15	DB 14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
PA1	0	0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0														P12	P11	P10	P9	P8	P7	P6	P5	P4	P3	P2	P1	C4(0)	C3(0)	C2(1)	C1(0)

													FF	RAC2	REG	SISTE	ER (F	(3)													
\int	RESI	ERVED)										24-	BIT FI	RAC2 \	/ALUE	(FRA	C2)								ſ	DBB		CON BI		
DB3	DB30	DB29	DB28	DB 27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB 14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
0	0	0	0	F24	F23	F22	F21	F20	F19	F18	F17	F16	F15	F14	F13	F12	F11	F10	F9	F8	F7	F6	F5	F4	F3	F2	F1	C4(0)	C3(0)	C2(1)	C1(1)

MOD2 REGISTER (R4)

	RESI	ERVED)										24	4-BIT N	IOD2	VALUE	(MOD	2)								[DBB			TROL ITS	
DB31	DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB 14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
0	0	0	0	M24	M23	M22	M21	M20	M19	M18	M17	M16	M15	M14	M13	M12	M11	M10	M9	M8	M7	M6	M5	M4	M3	M2	M1	C4(0)	C3(1)	C2(0)	C1(0)
NOTE	:e																														

NOTES 1. DBB MEANS DOUBLE-BUFFERED BITS.

Figure 18. Register Summary for Register 0 (R0) to Register 4 (R4)

analog.com

Rev. 0 | 13 of 29

													RD	IVID	ER R	EGIS	TER	(R5)													
	MODES	RESERVED		CF		DBB	<u>-</u> P1	ERVED	2 DBB	REFERENCE DOUBLER DBB		5-BIT	R COL	JNTER	DBB				12	2-BIT C	LK₁ D	IVIDEF		JE			DBB		CON		
	סרסי	RESE		SETT	ING		LSB.	RESERV	RDIV2	REFE																			BI	TS	
DB3	DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
DL2	DL1	0	CPI4	CPI3	CPI2	CPI1	L1	0	U2	U1	R5	R4	R3	R2	R1	D12	D11	D10	D9	D8	D7	D6	D5	D4	D3	D2	D1	C4(0)	C3(1)	C2(0)	C1(1)

FUNCTION REGISTER (R6)

BLEED CURRENT DB31 DB30 DB29 DB28 DB27 DB26 DB2 BC8 BC7 BC6 BC5 BC4 BC3 BC						BLEED POLARITY	BLEED ENABLE	RESERVED	INT MODE	ABP	LOL ENABLE	SD RESET	CP THREE-STATE PD ON			RESE	RVED	I			LDP	PD POLARITY	POWER DOWN	CP THREE-STATE	COUNTER RESET		CONT BIT				
DB31	DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
ВС8	BC7	BC6	BC4	BC3	BC2	BC1	BP1	BE1	0	IM1	A1	LOL1	SD1	CP1	1	0	0	0	0	0	LDP2	LDP1	PP1	PD	C31	CR1	C4(0)	C3(1)	C2(1)	C1(0)	

CLOCK 2 REGISTER (R7)

	RESERVED		LD_ COUNT		LD_CLK_SEL		KESEKVED		N DELAY	SVIA SO		CL DIVID MOI	ER				12	:-BIT C	:LK ₂ D	IVIDEF	R VALL	JE					CLN DIV SEL		CONT BI		
DB3	I DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
0	0	CN3	CN2	CN1	LD1	0	0	ND2	ND1	PB2	PB1	C2	C1	D12	D11	D10	D9	D8	D7	D6	D5	D4	D3	D2	D1	CS2	CS1	C4(0)	C3(1)	C2(1)	C1(1)

RESERVED REGISTER (R8)

\int													RESE	RVED															CONT		
DB31	DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	C4(1)	C3(0)	C2(0)	C1(0)

RESERVED REGISTER (R9)

	LD BIAS													RESE	RVED														CONT BI		
DB31	DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
LB2	LB1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	C4(1)	C3(0)	C2(0)	C1(1)

NOTES 1. DBB MEANS DOUBLE-BUFFERED BITS.

Figure 19. Register Summary for Register 5 (R5) to Register 9 (R9)

RESERVED REGISTER (R10)

\int													RESE	RVED																TROL TS	
DB3 [.]	1 DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB 22	DB 21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB 10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	C4(1)	C3(0)	C2(1)	C1(0)

RESERVED REGISTER (R11)

\bigcap													RESE	RVED																TROL TS	
DB31	DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB 22	DB 21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
PDS	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	C4(1)	C3(0)	C2(1)	C1(1)

MUXOUT REGISTER (R12)

	MU	хоит		LOGIC LEVEL		RESE	RVED		MAIN RESET	RESERVED	LE SELECT			READ SEL	BACK ECT							RESE	RVED							TROL TS	
DB31	DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB 22	DB 21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB 10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
M4	M3	M2	M1	ш	0	0	0	0	MR1	0	L1	R6	R5	R4	R3	R2	R1	0	0	0	0	0	0	0	0	0	0	C4(1)	C3(1)	C2(0)	C1(0)

RESERVED REGISTER (R13)

\bigcap													RESE	RVED																TROL ITS		
DB31	DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB 22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB 10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0	
0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	C4(1)	C3(1)	C2(0)	C1(1)	52

Figure 20. Register Summary for Register 10 (R10) to Register 13 (R13)

REGISTER 0 (R0) MAP

Frequency changes occur only on a write to Register 0.

Variable Modulus

Register 0, Bit 28 = 0 enables the 25-bit fixed modulus. Register 0, Bit 28 = 1 enables the variable modulus. See the N Divider and R Counter section for more information.

INT Value

Register 0, Bits[19:4] set the INT value. See the N Divider and R Counter section for more information.

REGISTER 1 (R1) MAP

DITHER2

Set Register 1, Bit 31 = 1 to enable the Σ - Δ modulator dither. Enabling DITHER2 can reduce fractional spurs.

FRAC1

Register 1, Bits[28:4] set the FRAC1 value. See the N Divider and R Counter section for more information. When using a fixed modulus, Bits[28:4] are the FRAC value.

23

024

REGISTER MAPS

													I	NT R	EGIS	STEF	R (R0)													
RESE	RVI	ĒD	VARIABLE MODULUS			R	ESER	VED									16	-BIT II	NTEGE	ER VA	LUE (INT)								TROL ITS	
DB31 D	B30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
0	0	0	V1	0	0	0	0	0	0	0	0	N16	N15	N14	N13	N12	N11	N10	N9	N8	N7	N6	N5	N4	N3	N2	N1	C4(0)	C3(0)	C2(0)) C1(0)
		_	•									ſ								Υ								,			
		(V1			E MOE		_		(N1		15	N14	N13	N12	N11	N10		N5	N4		13	N2	N1		NTEGE						
		0	1		KED M				-																			1			
		$\lfloor 1 \rfloor$	VAF	RIABL	E MOE	DULUS			0		0 D	0 0	0 0	0 0	0	0	•••	0	0		0 0	0 0	0 1		ΙΟΤ ΑΙ ΙΟΤ ΑΙ						
									0		0	0	0	0	0	0		0	0		0	1	0								
									.																						
									0		0	0	0	0	0	0		1	0		0	1	1	N		LOW	ED				
									0		0	0	0	0	0	0		1	0		1	0	0	2	0						
									0		0	0	0	0	0	0		1	0		1	0	1	2	1						
									·		•	•	٠	٠	•	•		٠	•		•	•	•								
									0		D	0	0	0	0	1		1	1		1	1	0	1	022						
									0		0	0	0	0	0	1		1	1		1	1	1		023						
									0		0	0	0	0	1	0		0	0		0	0	0	N	ΙΟΤ ΑΙ	LOW	ED				
											1	1	1	1	1	1		1	1		1	1	1			LLOW	ED ,)			
																					F F FR F	PRESC	CALER	4/5: 2 8/9: 6 N MOE 4/5: 2	:0 ≤ IN :4 ≤ IN DE :3 ≤ IN :5 ≤ IN	T≤10 T≤51	23				

Figure 21. Register 0 (R0) Map

FRAC1 REGISTER (R1)

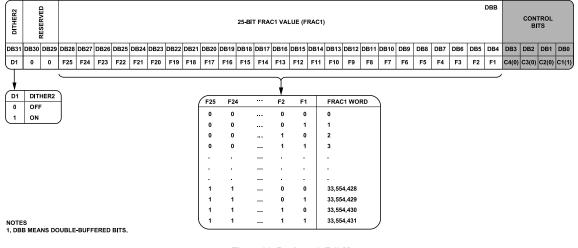


Figure 22. Register 1 (R1) Map

REGISTER 2 (R2) MAP

Phase Adjust

Set Register 2, Bit 31 to 1 to enable phase adjust. Phase adjust increases the phase of the output relative to the current phase. The phase change occurs after a write to Register 0.

Phase Shift = (Phase Value × 360°)/ 2^{12} (5)

Phase Value

Register 2, Bits[15:4] set the phase value for phase adjust. For example, setting the phase value = 512 increases the output phase by 45° .

If phase adjust is not used, set the phase value to 0.

REGISTER 3 (R3) MAP

FRAC2

Register 3, Bits[27:4] set the FRAC2 value. See the N Divider and R Counter section for more information. When using a fixed modulus, FRAC2 is ignored.

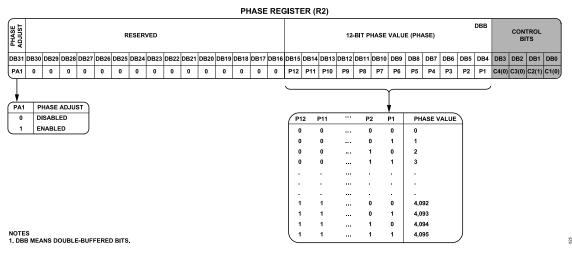


Figure 23. Register 2 (R2) Map

FRAC2 REGISTER (R3)

\int	RES	ERVE	þ										24	1-BIT I	RAC2	VALU	E (FR	AC2)									DBB		CON ⁻ BI		
DB3	DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
0	0	0	0	F24	F23	F22	F21	F20	F19	F18	F17	F16	F15	F14	F13	F12	F11	F10	F9	F8	F7	F6	F5	F4	F3	F2	F1	C4(0)	C3(0)	C2(1)	C1(1)

				Ĭ	
F24	F23	•••	F2	F1	FRAC2 WORD
0	0		0	0	0
0	0		0	1	1
0	0		1	0	2
0	0		1	1	3
· ·	•		·	÷	
	•	•••	•	•	
· ·	•		•	•	
1	1		0	0	16,777,212
1	1		0	1	16,777,213
1	1		1	0	16,777,214
	1		1	1	16,777,215

Figure 24. Register 3 (R3) Map

REGISTER 4 (R4) MAP

MOD2

Register 4, Bits[27:4] set the MOD2 value. See the N Divider and R Counter section for more information. When using a fixed modulus, MOD2 is ignored.

REGISTER 5 (R5) MAP

DLD Modes

Register 5, Bits[31:30] set the digital lock detect (DLD) pin state. For normal digital lock detect, set Register 5, Bits[31:30] = 0b01. Other options tristate the pin and force a high or low logic level, as shown in Figure 26.

CP Current Setting

Register 5, Bits[28:25] set the charge pump current. Set these bits to the charge pump current that the loop filter is designed for based

on the application of the user. The recommended practice is to design the loop filter for a charge pump current of 2.4 mA or 2.7 mA and then use the programmable charge pump current to fine tune the loop filter frequency response.

LSB_P1

Register 5, Bit 24 = 0 enables a 26^{th} bit in the fixed modulus MOD value. Enabling the 26^{th} bit reduces fractional spurs but the reduction also adds a fixed $f_{PFD}/2^{26}$ frequency offset to the output frequency. To disable this frequency offset, set Register 5, Bit 24 = 1.

Prescaler

The prescaler, at the input to the N divider, divides down the f_{RFIN} signal so that the N divider can operate correctly. The prescaler is based on a synchronous 4/5 core. The prescaler setting affects the RF output frequency and the minimum and maximum INT value as follows:

027

REGISTER MAPS

- ▶ Integer-N mode: $20 \le INT \le 511$, $f_{RFIN MAX} = 10 \text{ GHz}$
- Fractional-N mode: $23 \le INT \le 511$, $f_{RFIN MAX}^{-} = 10 \text{ GHz}$

RDIV2

Register 5, Bit 22 controls the reference divide by 2 block. See the N Divider and R Counter section for more information. This feature can provide a 50% duty cycle signal to the PFD.

Reference Doubler

Register 5, Bit 21 controls the reference doubler block. See the N Divider and R Counter section for more information.

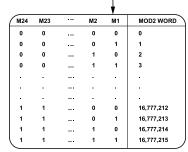
R Counter

Register 5, Bits[20:16] control the R counter value. See the N Divider and R Counter section for more information.

CLK₁ Divider

Register 5, Bits[15:4] control the CLK_1 divider value. See the Phase Resync section for more information.

	MOD2 REGISTER (R4)																														
	RESERVED 24-BIT MOD2 VALUE (MOD2)														DBB			TROL TS													
DB31	DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
0	0	0	0	M24	M23	M22	M21	M20	M19	M18	M17	M16	M15	M14	M13	M12	M11	M10	M9	M8	M7	M6	M5	M4	M3	M2	M1	C4(0)	C3(1)	C2(0)	C1(0)
																¥															



NOTES 1. DBB MEANS DOUBLE-BUFFERED BITS.

Figure 25. Register 4 (R4) Map

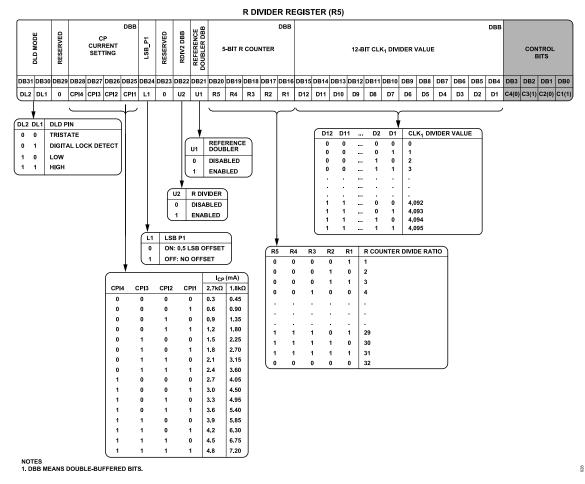


Figure 26. Register 5 (R5) Map

REGISTER 6 (R6) MAP

Bleed Current

Register 6, Bits[31:24] set the bleed current. If the PD polarity is set to positive, the optimum bleed current is set by

Bleed Value = floor(90 × (f_{PFD} /100 MHz) × ($I_{CP CODE}$ + 1)/16) (6)

where:

Bleed Value is the value programmed to Register 6, Bits[31:24]. $I_{CP CODE}$ is the charge pump current setting programmed to Register 5, Bits[28:25]. f_{PED} is the PFD frequency in MHz.

TPFD IS the PFD frequency in MHZ.

If the PD polarity is set to negative, the optimum bleed current is set by

Bleed Value = floor(144 × (f_{PFD} /100 MHz) × (I_{CP_CODE} (7) +1)/16)

Bleed Polarity

Register 6, Bit 23 controls the polarity of the bleed current. Negative polarity is the typical usage.

Bleed Enable

In fractional-N mode of operation, charge pump linearity (and ultimately phase noise and spurious performance) is improved if the VCO and reference inputs to the phase detector operate with a phase offset. This phase offset is implemented by adding a constant bleed current at the output of the charge pump. Use bleed only when operating in fractional-N mode, that is, FRAC1 or FRAC2 not equal to 0. Set Register 6, Bit 22 = 1 to enable bleed.

INT Mode

Register 6, Bit 20 completely disables the fractional-N Σ - Δ modulator (SDM). Setting Register 6, Bit 20 = 1 disables the SDM so the ADF41510 operates purely in Integer-N mode. Disabling the SDM improves phase noise performance and changes the frequency resolution to f_{PFD}.

ABP

Register 6, Bit 19 affects the anti-backlash pulse (ABP) width. The recommended setting for best figure of merit (FOM) is narrow (Register 6, Bit 19 = 1).

Loss of Lock (LOL) Enable

If digital lock detect is asserted when loss of lock is enabled and the reference signal is removed, digital lock detect goes low. Set Register 6, Bit 18 = 1 to enable loss of lock (recommended).

Sigma-Delta (SD) Reset

When Register 6, Bit 17 = 0 on a write to Register 0, the SDM is temporarily set to a fractional value of 0. The SD reset ensures a consistent fractional spur pattern but also results in a glitch in the output frequency when the N divider momentarily outputs FRAC = 0. Remove this glitch by setting Register 6, Bit 17 = 1 (recommended setting).

CP Three-State, PD on

When Register 6, Bit 16 = 1, the charge pump is in three-state mode but the phase detector (PD) is still operational. Set Register 6, Bit 16 = 0 for normal operation.

Lock Detector Precision (LDP)

Register 6, Bits[9:8] and Register 9, Bits[31:30] control the sensitivity of the digital lock detector. Lock detect precision (Register 6, Bits[9:8]) in conjunction with lock detector bias (Register 9, Bits[31:30]) adjusts the width of the digital lock detector window. Lock is declared when the PFD reference arrival time and divided VCO input arrival times consistently differ by less than the LDP value. Small LDP settings may cause a false out of lock indication when used with large bleed currents. See the Lock Detector section for more information.

Phase Detector (PD) Polarity

If using a noninverting loop filter and a VCO with a positive tuning slope, set the PD polarity to positive.

If using an inverting loop filter and a VCO with a negative tuning slope, set the PD polarity to positive.

If using a noninverting loop filter and a VCO with a negative tuning slope, set the PD polarity to negative.

If using an inverting loop filter and a VCO with a positive tuning slope, set the PD polarity to negative.

Power Down

Set Register 6, Bit 6 = 1 to perform a software power-down. All circuit blocks are disabled, and the chip enters a low power state drawing approximately 4 mA. Set Register 6, Bit 6 = 0 to reenable the chip. Register values are not lost during power-down. Only one power-down mode is available via Register 11, Bit 31. Set Register 11, Bit 31 = 1 to leave the internal 1.8 V N divider regulator on during power-down.

Note that Register 12, Bit 20 must be set to 0 when writing this power-down bit. Otherwise, the chip cannot be powered back on again by setting Register 6, Bit 6 = 0.

CP Three-State

Setting Register 6, Bit 5 = 1 puts the charge pump into three-state mode. Set Register 6, Bit 5 = 0 for normal operation.

Counter Reset

Setting Register 6, Bit 4 = 1 holds the N divider and R counter in reset, which results in no signals being received at the PFD.

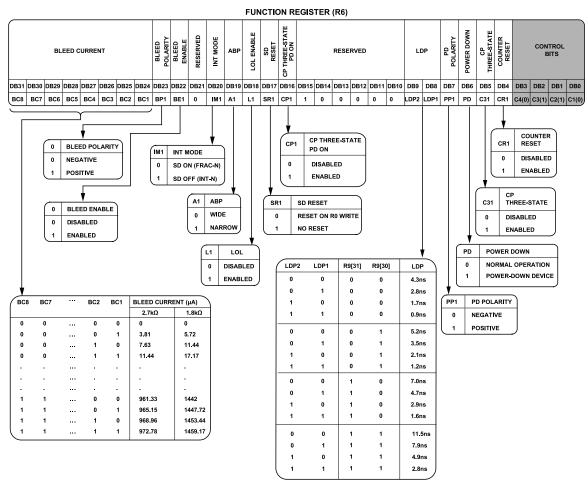


Figure 27. Register 6 (R6) Map

REGISTER 7 (R7) MAP

Lock Detector Count (LD_COUNT)

LD_COUNT sets the initial value of the lock detect counter. See the Lock Detector section for more information about the operation of the lock detector.

Lock Detect Clock Select (LD_CLK_SEL)

The lock detector checks for lock on every phase comparison cycle when LD CLK SEL = 1. Otherwise, the lock detector checks for lock on every 32^{nd} cycle. Use LD CLK SEL = 1 to speed up declaration of lock at the cost of reduced lock indication stability during frequency changes.

SDM to N Divider Timing Adjustment (N Delay)

This control adjusts the timing between the SDM output and the N divider. Set these bits to 0b00.

Prescaler (PS) Bias

Set these bits to 0b10.

CLK Divider Mode

Setting Register 7, Bits[19:18] = 0b10 enables a phase resync. See the Phase Resync section for more information.

When not using phase resync, set Register 7, Bits[19:18] = 0b00.

CLK₂ Divider Value

Register 7, Bits[17:6] control the CLK_2 divider value. The CLK_2 divider value controls the timing of the phase resync pulse. See the Phase Resync section for more information.

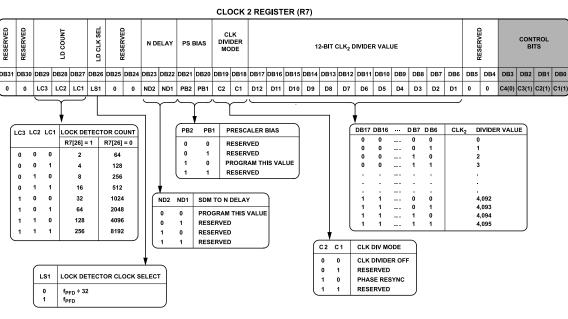


Figure 28. Register 7 (R7) Map

REGISTER 8 (R8) MAP

Set all reserved bits to zero.

REGISTER 9 (R9) MAP

Lock Detector Bias

The lock detector window size is set by adjusting the lock detector bias in conjunction with the lock detector precision bits (Register 6, Bits[9:8]). See the Lock Detector section.

$\left[\right]$													RES	BERVE	D														CONT BI			
DB31	DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0	
0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	C4(1)	C3(0)	C2(0)	C1(0)	034

Figure 29. Register 8 (R8) Map

LOCK	DETECTOR	BIAS	REGISTER	(R9)

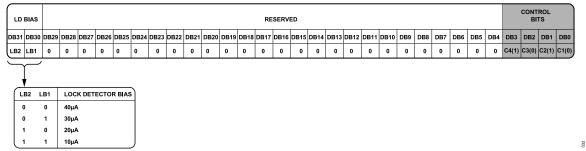


Figure 30. Register 9 (R9) Map

REGISTER 10 (R10) MAP

Set all reserved bits to zero.

REGISTER 11 (R11) MAP

Power-Down Select

Only one power-down option is available. Program Register 11, Bit 31 = 1. Set Register 6, Bit 6 = 1 to power down the device.

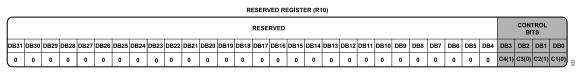


Figure 31. Register 10 (R10) Map

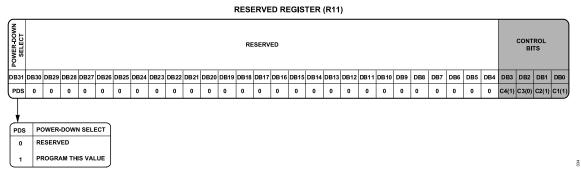


Figure 32. Register 11 (R11) Map

REGISTER 12 (R12) MAP

MUXOUT

Register 12, Bits[31:28] select the MUXOUT signal. Register data can be read either by selecting the serial data output or via a readback. Serial data output sends the 32 bits of register data that was written in the previous access. A readback sends the data as defined by the readback select bits, Register 12, Bits[19:14].

Logic Level

Register 12, Bit 27 selects the DLD and MUXOUT logic level.

Main Reset

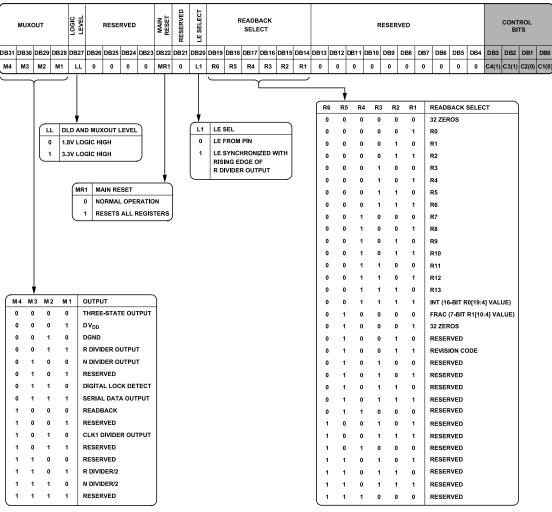
Register 12, Bit 22 = 1 resets all registers to all zeros.

LE Select

Register 12, Bit 20 = 1 synchronizes the rising edge of LE on an SPI write with the falling edge of the reference signal. This recommended setting ensures there is no glitch from asynchronous loading. Set Register 12, Bit 20 = 0 if it is necessary to write data into the ADF41510 when no reference is present.

Readback Select

Register 12, Bits[19:14] select the value to be read back. For more information, see the Readback section.



MUXOUT REGISTER (R12)

Figure 33. Register 12 (R12) Map

REGISTER 13 (R13) MAP

Set all reserved bits to zero.

RESERVED REGISTER (R13)

\bigcap	RESERVED													CON BI																	
DB31	DB30	DB29	DB28	DB27	DB26	DB25	DB24	DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
O	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	C4(1)	C3(1)	C2(0)	C1(1)

Figure 34. Register 13 (R13) Map

APPLICATIONS INFORMATION

INITIALIZATION SEQUENCE

The following sequence of registers is the correct sequence for initial power-up of the ADF41510 after the correct application of voltages to the supply pins:

- 1. Register 13
- 2. Register 12
- 3. Register 11
- 4. Register 10
- 5. Register 9
- 6. Register 8
- 7. Register 7
- 8. Register 6
- 9. Register 5
- **10.** Register 4
- 11. Register 3
- 12. Register 2
- 13. Register 1
- 14. Register 0

RF SYNTHESIZER: A WORKED EXAMPLE OF 25-BIT FIXED MODULUS MODE

The following equation governs how to program the synthesizer:

$$RF_{OUT} = (INT + (FRAC1/2^{25})) \times f_{PFD}$$

where:

 RF_{OUT} is the RF output frequency. INT is the integer division factor. FRAC1 is the fractional numerator. f_{PFD} is the PFD frequency.

For example, in a system where a 9.102 GHz RF output frequency (RF_{OUT}) is required and a 100 MHz reference frequency input (REF_{IN}) is available, the frequency resolution, f_{RES} , is

 $f_{RES} = REF_{IN}/2^{25}$

 $f_{RES} = 100 \text{ MHz}/2^{25}$

= 2.98 Hz

From Equation 1 and Equation 2,

 f_{PFD} = (100 MHz × (1 + 0)/1) = 100 MHz 9.102 GHz = 100 MHz × (N + FRAC/2²⁵)

Calculating the INT and FRAC values,

 $INT = int(RF_{OUT}/f_{PFD}) = 91$

 $FRAC1 = (int(RF_{OUT}/f_{PFD}) - INT) \times 2^{25} = 671088.64 \approx 671089$

where:

INT is the 16-bit INT value in Register 0. *FRAC1* is the 25-bit FRAC1 value in Register 1. int() makes an integer of the argument in parentheses. Note that 671088.64 is rounded to 671,089, resulting in a small frequency error. For exact frequency, use the variable modulus mode.

RF SYNTHESIZER: A WORKED EXAMPLE OF VARIABLE MODULUS MODE

The following is an example how to program the ADF41510 synthesizer:

 $RF_{OUT} = f_{PFD} \times (INT + (FRAC1 + (FRAC2/MOD2))/2^{25})$ (9)

where:

 RF_{OUT} is the output frequency of the external VCO. INT is a 16-bit value set by Bits[19:4] in Register 0. In Integer-N mode, INT is 20 to 511, and in fractional-N mode, INT is 23 to 511. FRAC1 is a 25-bit value set by Bits[28:4] in Register 1. FRAC2 is a 24-bit value set by Bits[27:4] in Register 3. MOD2 is a 24-bit value set by Bits[27:4] in Register 4. f_{PED} is the PFD frequency.

For example, in a system where a 9.102 GHz $\rm RF_{OUT}$ is required and a 100 MHz $f_{\rm PFD}$ is available,

 $INT = int(RF_{OUT}/f_{PFD}) = 91 \ FRAC1 = int(((RF_{OUT}/f_{PFD}) - INT) \times 2^{25}) = 671,088$ (10)

where int() makes an integer of the argument in parentheses.

Remainder = FRAC2/MOD2 = 0.64

where: *FRAC2* = 64. *MOD2* = 100.

MODULUS

The choice of modulus (MOD) depends on the reference signal (REF_IN) available and the channel resolution (f_{RES}) required at the RF output.

REFERENCE DOUBLER AND REFERENCE DIVIDER

The on-chip reference doubler allows the input reference signal to be doubled. Doubling is useful for increasing the PFD comparison frequency. Setting the PFD frequency higher improves the noise performance of the system. Doubling the PFD frequency usually improves noise performance by 3 dB. It is important to note that the reference input cannot operate above 225 MHz when the reference doubler is on. The PFD maximum operating frequency is 250 MHz (Integer-N mode) or 125 MHz (fractional-N mode) due to a limitation in the speed of the Σ - Δ circuit.

The reference divide by 2 divides the reference signal by 2, resulting in a 50% duty cycle PFD frequency.

SPUR MECHANISMS

This section describes the two different spur mechanisms that arise with a PLL, and how to minimize them in the ADF41510.

(11)

(8)

APPLICATIONS INFORMATION

Integer Boundary Spurs

Interactions between the RF VCO frequency and the reference frequency cause integer boundary spurs. When these frequencies are not integer related (the point of a fractional-N synthesizer), spur sidebands appear on the VCO output spectrum at an offset frequency that corresponds to the beat note or difference frequency between an integer multiple of the reference and the VCO frequency. These spurs are attenuated by the loop filter and are more noticeable on channels close to integer multiples of the reference where the difference frequency can be inside the loop bandwidth.

Reference Spurs

Reference spurs are generally not a problem in fractional-N synthesizers because the reference offset is far outside the loop bandwidth. However, any reference feedthrough mechanism that bypasses the loop can cause a problem. Feedthrough of low levels of on-chip reference switching noise, through the $RF_{IN}A$ pin or the $RF_{IN}B$ pin back to the VCO, can result in reference spur levels as high as -90 dBc. PCB layout must ensure adequate isolation between VCO traces and the input reference to avoid a possible feedthrough path on the board.

PHASE RESYNC

The output of a 25-bit fractional-N PLL can settle to any of the 2²⁵ phase offsets with respect to the input reference. The phase resync feature in the ADF41510 produces a consistent output phase offset with respect to the input reference. This consistent output phase offset with respect to the input reference is necessary in applications where the output phase and frequency are important, such as digital beamforming. See the Phase Programmability section to program a specific RF output phase when using phase resync.

Phase resync is enabled by setting Register 7, Bits[19:18] = 0b10. When phase resync is enabled, an internal timer generates sync signals at intervals of t_{SYNC} given by the following formula:

(12)

$$t_{SYNC} = CLK_1 \times CLK_2 \times t_{PFD}$$

where:

 CLK_1 is the decimal value programmed in Register 5, Bits[15:4]. CLK_2 is the decimal value programmed in Register 7, Bits[17:6]. t_{PFD} is the PFD reference period (1/ f_{PFD}).

When a new frequency is programmed, the second sync pulse after the LE rising edge resynchronizes the output phase to the reference. Program the t_{SYNC} time to a value that is at least as long as the worst case lock time to guarantee that the phase resync occurs after the last cycle slip in the PLL settling transient.

In the example shown in Figure 35, t_{SYNC} is set to 550 µs. The second sync pulse and any later sync pulses are ignored.

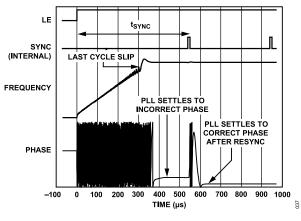
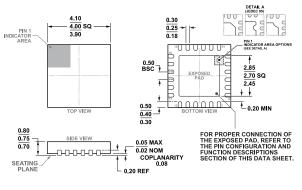


Figure 35. Phase Resync Example

Phase Programmability

The phase word in Register 2 controls the RF output phase. As this word is changed from 0 to 2^{12} , the RF output phase changes over a 360° range in steps of phase value × $360^{\circ}/2^{12}$.

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-220-WGGD-8

Figure 36. 24-Lead Lead Frame Chip Scale Package [LFCSP] 4 mm × 4 mm Body and 0.75 mm Package Height (CP-24-8) Dimensions shown in millimeters

Updated: August 09, 2023

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Packing Quantity	Package Option
ADF41510BCPZ	-40°C to +105°C	24-Lead LFCSP (4 mm × 4 mm × 0.75 mm w/ EP)	Tray, 490	CP-24-8
ADF41510BCPZ-RL7	-40°C to +105°C	24-Lead LFCSP (4 mm × 4 mm × 0.75 mm w/ EP)	Reel, 1500	CP-24-8

¹ Z = RoHS-Compliant Part.

EVALUATION BOARDS

Parameter ¹	Description
EV-ADF41510SD1Z	Evaluation Board Without VCO.
EV-ADF41510SD2Z	Evaluation Board with On-Board VCO.

¹ Z = RoHS-Compliant Part.

